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CONTENTS

15 SEPTEMBER 2000-II

RAPID COMMUNICATIONS

Electronic structure: wide-band, narrow-band, and strongly correlated systems

- Charge ordering in a quasi-two-dimensional organic conductor R7679
K. Miyagawa, A. Kawamoto, and K. Kanoda
- Optical bistability in finite-size nonlinear bidimensional photonic crystals doped by a microcavity R7683
E. Centeno and D. Felbacq
- Final-state interaction in Compton scattering from electron liquids R7687
C. Sternemann, K. Hämäläinen, A. Kaprolat, A. Soininen, G. Döring, C.-C. Kao, S. Manninen,
and W. Schülke
- Electronic states in Rb_1C_{60} studied by EPR under pressure: 3D Mott-Hubbard system R7691
Hirokazu Sakamoto, Shigenori Kobayashi, Kenji Mizoguchi, Mayumi Kosaka, and Katsumi Tanigaki
- Loss structures in the photoemission spectra of MnO : A careful analysis of peak intensities R7695
Luigi Sangaletti, Paul S. Bagus, and Fulvio Parmigiani
- Exact diagonalization study of rare events in disordered conductors R7699
V. Uski, B. Mehlig, R. A. Römer, and M. Schreiber
- X-ray natural circular dichroism R7703
Paolo Carra and Robert Benoist

Semiconductors I: bulk

- Low-density framework form of crystalline silicon with a wide optical band gap R7707
Jan Gryko, Paul F. McMillan, Robert F. Marzke, Ganesh K. Ramachandran, Derek Patton, Sudip K. Deb,
and Otto F. Sankey

Semiconductors II: surfaces, interfaces, microstructures, and related topics

- Effects of surface hydrogenation on initial reaction processes of transition-metal Ni and Ti adatoms on $\text{Si}(001)$ surfaces R7711
Shin'ichi Higai and Takahisa Ohno
- $\text{Si}(100)\text{-c}(4\times 8)$ reconstruction formed in a highly nonequilibrium process R7715
Y. F. Zhao, H. Q. Yang, and S. J. Pang
- Surface reconstructions for $\text{InAs}(001)$ studied with density-functional theory and STM R7719
C. Ratsch, W. Barvosa-Carter, F. Grosse, J. H. G. Owen, and J. J. Zinck
- C incorporation in epitaxial $\text{Ge}_{1-y}\text{C}_y$ layers grown on $\text{Ge}(001)$: An *ab initio* study R7723
D. Gall, J. D'Arcy-Gall, and J. E. Greene
- Shot noise at hopping via two sites R7727
Yusuf A. Kinkhabwala and Alexander N. Korotkov

